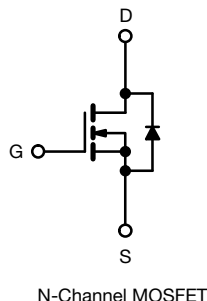


EF Series Power MOSFET With Fast Body Diode

Thin-Lead TO-220 FULLPAK



FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low effective capacitance ($C_{o(er)}$)
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

PRODUCT SUMMARY

| | | |
|---|-----------------|-------|
| V_{DS} (V) at T_J max. | 850 | |
| $R_{DS(on)}$ typ. (Ω) at 25 °C | $V_{GS} = 10$ V | 0.263 |
| Q_g max. (nC) | 63 | |
| Q_{gs} (nC) | 9 | |
| Q_{gd} (nC) | 19 | |
| Configuration | Single | |

ORDERING INFORMATION

| | |
|---------------------------------|--------------------------|
| Package | Thin-Lead TO-220 FULLPAK |
| Lead (Pb)-free and halogen-free | SiHA17N80AEF-GE3 |

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|---|------------------|----------------|----------------|
| Drain-source voltage | V_{DS} | 800 | V |
| Gate-source voltage | V_{GS} | ± 30 | |
| Continuous drain current ($T_J = 150$ °C) ^e | V_{GS} at 10 V | $T_C = 25$ °C | A |
| | | $T_C = 100$ °C | |
| Pulsed drain current ^a | I_{DM} | 32 | |
| Linear derating factor | | 0.27 | W/°C |
| Single pulse avalanche energy ^b | E_{AS} | 127 | mJ |
| Maximum power dissipation | P_D | 34 | W |
| Operating junction and storage temperature range | | T_J, T_{stg} | -55 to +150 °C |
| Drain-source voltage slope | dv/dt | $T_J = 125$ °C | V/ns |
| Reverse diode dv/dt ^d | | | |
| Soldering recommendations (peak temperature) ^c | | For 10 s | 260 °C |
| Mounting torque | M3 screw | - | 0.6 Nm |


Notes

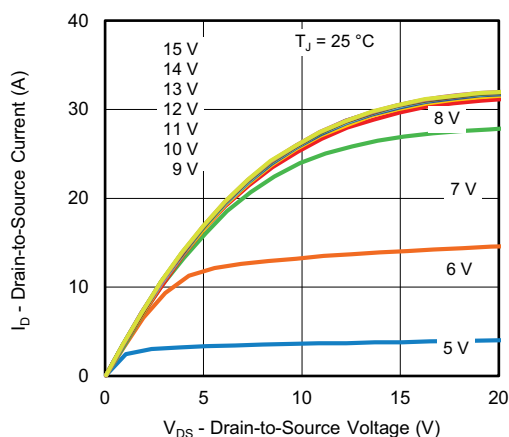
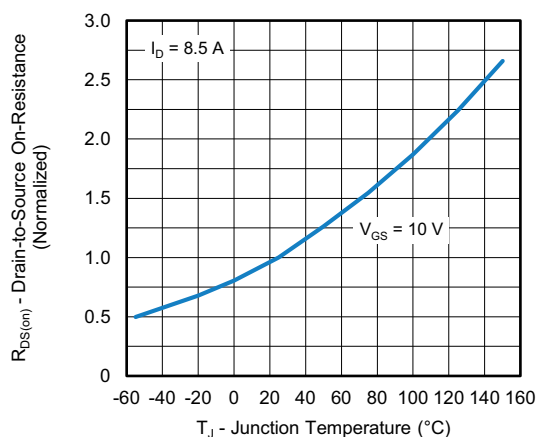
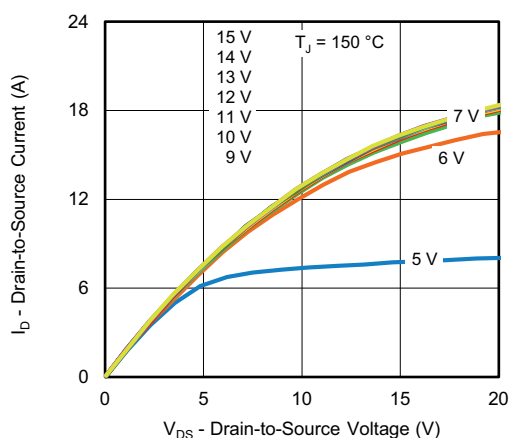
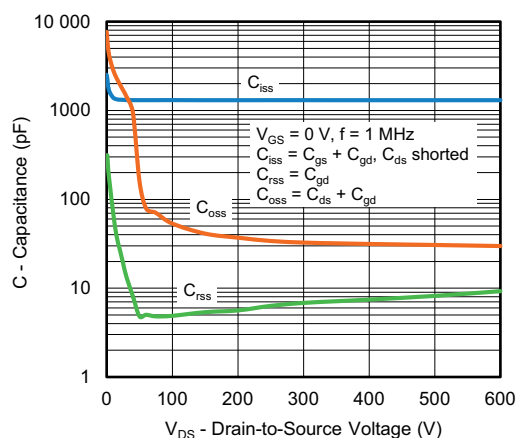
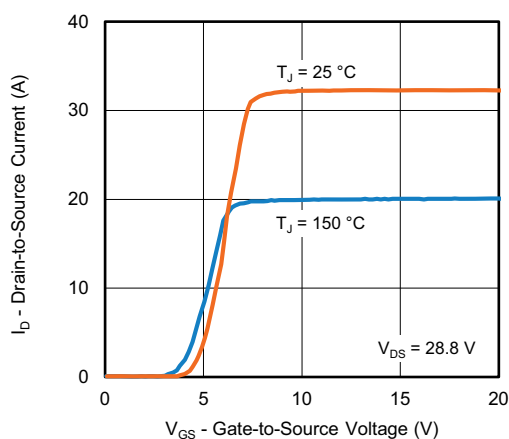
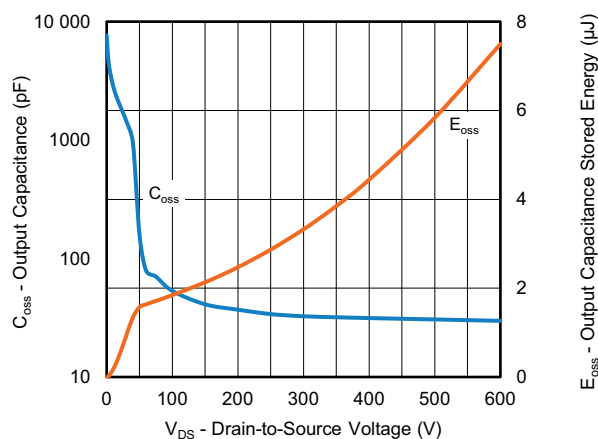
- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 3$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $di/dt = 450$ A/ μ s, starting $T_J = 25$ °C
- Limited by maximum junction temperature

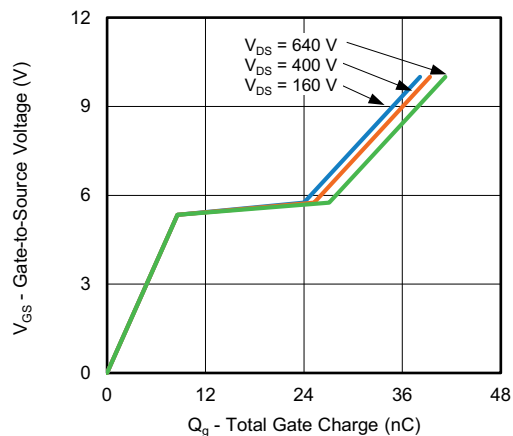
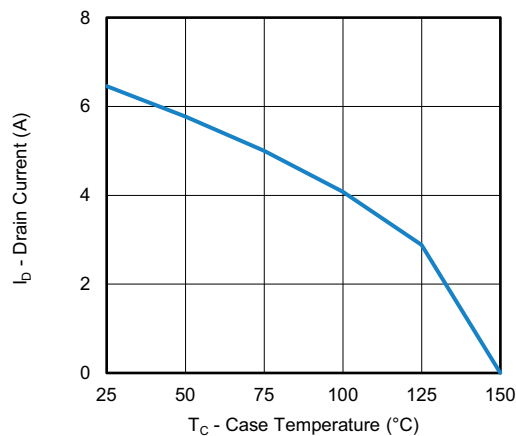
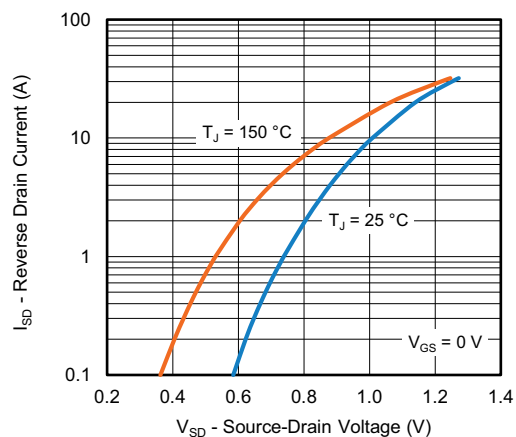
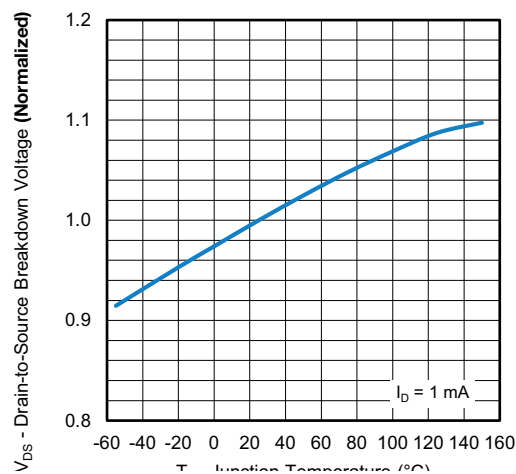
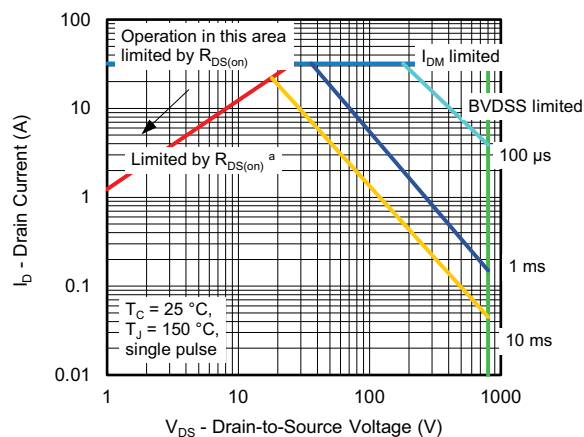
**THERMAL RESISTANCE RATINGS**

| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
|----------------------------------|------------|------|------|------|
| Maximum junction-to-ambient | R_{thJA} | - | 65 | °C/W |
| Maximum junction-to-case (drain) | R_{thJC} | - | 3.7 | |

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|--|---------------------|--|--|------|-------|-----------|---------------------|
| Static | | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$ | | 800 | - | - | V |
| V_{DS} temperature coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | | - | 0.8 | - | V/ $^\circ\text{C}$ |
| Gate-source threshold voltage (N) | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | | 2 | - | 4 | V |
| Gate-source leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| | | $V_{GS} = \pm 30\text{ V}$ | | - | - | ± 1 | μA |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = 640\text{ V}$, $V_{GS} = 0\text{ V}$ | | - | - | 1 | μA |
| | | $V_{DS} = 640\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ | | - | - | 2 | mA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 8.5\text{ A}$ | - | 0.263 | 0.305 | Ω |
| Forward transconductance ^a | g_{fs} | $V_{DS} = 10\text{ V}$, $I_D = 8.5\text{ A}$ | | - | 8.6 | - | S |
| Dynamic | | | | | | | |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$ | | - | 1300 | - | pF |
| Output capacitance | C_{oss} | | | - | 48 | - | |
| Reverse transfer capacitance | C_{rss} | | | - | 5 | - | |
| Effective output capacitance, energy related | $C_{o(er)}$ | $V_{DS} = 0\text{ V to } 480\text{ V}$, $V_{GS} = 0\text{ V}$ | | - | 39 | - | |
| Effective output capacitance, time related | $C_{o(tr)}$ | | | - | 240 | - | |
| Total gate charge | Q_g | $V_{GS} = 10\text{ V}$ | $I_D = 8.5\text{ A}$, $V_{DS} = 640\text{ V}$ | - | 42 | 63 | nC |
| Gate-source charge | Q_{gs} | | | - | 9 | - | |
| Gate-drain charge | Q_{gd} | | | - | 19 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 640\text{ V}$, $I_D = 8.5\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 9.1\text{ }\Omega$ | | - | 16 | 32 | ns |
| Rise time | t_r | | | - | 20 | 40 | |
| Turn-off delay time | $t_{d(off)}$ | | | - | 32 | 64 | |
| Fall time | t_f | | | - | 38 | 76 | |
| Gate input resistance | R_g | $f = 1\text{ MHz}$, open drain | | 0.2 | 0.5 | 1.1 | Ω |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous source-drain diode current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | | - | - | 6.5 | A |
| Pulsed diode forward current | I_{SM} | | | - | - | 32 | |
| Diode forward voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}$, $I_S = 8.5\text{ A}$, $V_{GS} = 0\text{ V}$ | | - | - | 1.2 | V |
| Reverse recovery time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}$, $I_F = I_S = 8.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 400\text{ V}$ | | - | 114 | 228 | ns |
| Reverse recovery charge | Q_{rr} | | | - | 0.7 | 1.4 | μC |
| Reverse recovery current | I_{RRM} | | | - | 12 | - | A |

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 10 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Typical Source-Drain Diode Forward Voltage

Fig. 11 - Temperature vs. Drain-to-Source Voltage

Fig. 9 - Maximum Safe Operating Area
Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

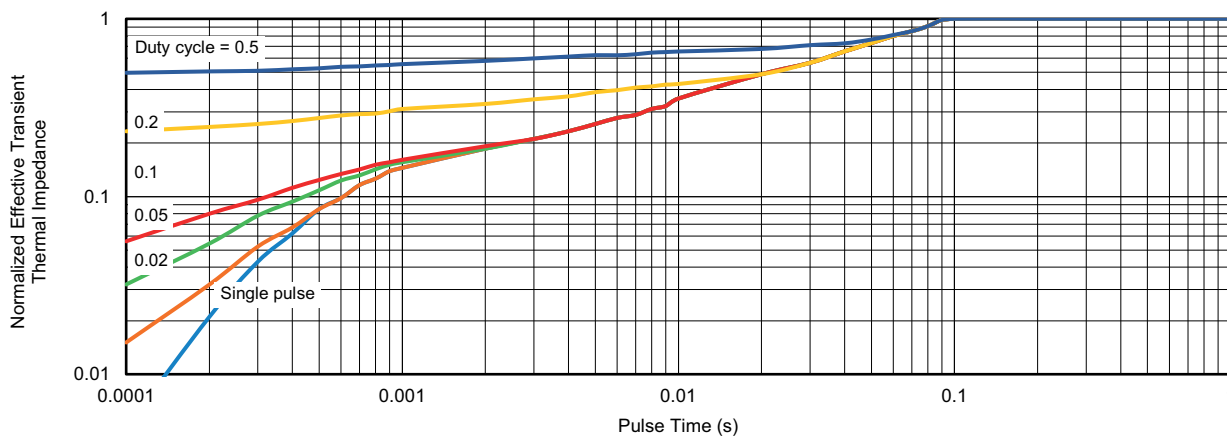

Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

Fig. 13 - Switching Time Test Circuit

Fig. 16 - Unclamped Inductive Waveforms

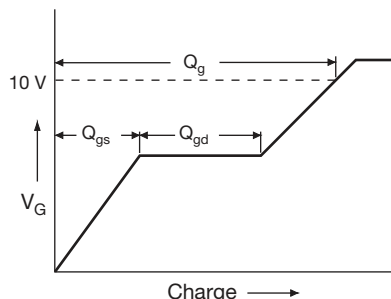
Fig. 14 - Switching Time Waveforms

Fig. 17 - Basic Gate Charge Waveform

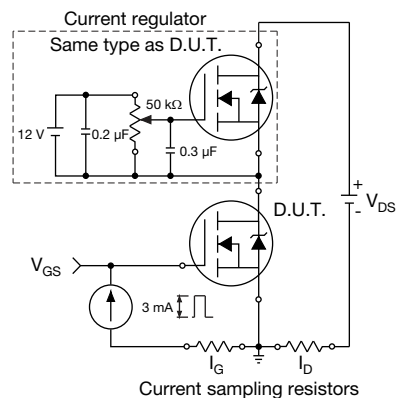
Fig. 15 - Unclamped Inductive Test Circuit

Fig. 18 - Gate Charge Test Circuit


Fig. 19 - For N-Channel

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TO-220 FULLPAK Thin Lead



| SYMBOL | DIMENSIONS | | | |
|--|-------------|-------|--------|-------|
| | MILLIMETERS | | INCHES | |
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.30 | 4.70 | 0.169 | 0.185 |
| A1 | 2.50 | 2.90 | 0.098 | 0.114 |
| A2 | 2.40 | 2.80 | 0.094 | 0.110 |
| b | 0.60 | 0.80 | 0.024 | 0.031 |
| b2 | 0.60 | 0.90 | 0.024 | 0.035 |
| c | - | 0.60 | - | 0.024 |
| D | 8.30 | 8.70 | 0.327 | 0.342 |
| d1 | 14.70 | 15.30 | 0.579 | 0.602 |
| d2 | 2.90 | 3.10 | 0.114 | 0.122 |
| d3 | 3.30 | 3.70 | 0.130 | 0.146 |
| E | 9.70 | 10.30 | 0.382 | 0.406 |
| e | 2.50 | 2.70 | 0.098 | 0.106 |
| L | 13.40 | 13.80 | 0.528 | 0.543 |
| L1 | 1.00 | 2.80 | 0.039 | 0.110 |
| Ø P | 3.00 | 3.40 | 0.118 | 0.134 |
| ECN: E20-0684-Rev. D, 28-Dec-2020 DWG: 6021 | | | | |



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